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ptember 2011 Product data sheet

1. Product profile

1.1 General description

NPN silicon planar epitaxial transistor in a 4-pin dual-emitter SOT143R plastic package.

1.2 Features and benefits

- High power gain
- Low noise figure
- High transition frequency
- Gold metallization ensures excellent reliability

1.3 Applications

- Intended for Radio Frequency (RF) front end applications in the GHz range, such as:
 - analog and digital cellular telephones
 - cordless telephones (Cordless Telephone (CT), Personal Communication Network (PCN), Digital Enhanced Cordless Telecommunications (DECT), etc.)
 - radar detectors
 - pagers
 - ◆ Satellite Antenna TeleVision (SATV) tuners
 - repeater amplifiers in fiber-optic systems

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-	15	V
V_{CEO}	collector-emitter voltage	open base	-	-	6	V
I _C	collector current (DC)		-	-	35	mA
P _{tot}	total power dissipation	T _{sp} ≤ 90 °C	[1] -	-	210	mW
h _{FE}	DC current gain	$I_C = 15 \text{ mA}; V_{CE} = 3 \text{ V};$ $T_j = 25 \text{ °C}$	60	100	200	
C _{CBS}	collector-base capacitance	V _{CB} = 5 V; f = 1 MHz; emitter grounded	-	0.26	0.4	pF
f _T	transition frequency	$I_C = 15 \text{ mA}; V_{CE} = 3 \text{ V};$ $f = 1 \text{ GHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	14	-	GHz



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
G_{max}	maximum power gain ^[2]	I_{C} = 15 mA; V_{CE} = 3 V; f = 1.8 GHz; T_{amb} = 25 °C	-	18.3	-	dB
S ₂₁ ²	insertion power gain	$\begin{split} &I_C = 15 \text{ mA; } V_{CE} = 3 \text{ V;} \\ &f = 1.8 \text{ GHz; } T_{amb} = 25 \text{ °C;} \\ &Z_S = Z_L = 50 \Omega \end{split}$	-	14	-	dB
NF	noise figure	$\Gamma_{\text{s}} = \Gamma_{\text{opt}}; \ I_{\text{C}} = 3 \ \text{mA}; \ V_{\text{CE}} = 3 \ \text{V}; \ f = 2 \ \text{GHz}$	-	1.1	-	dB

^[1] T_{sp} is the temperature at the soldering point of the collector pin.

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Symbol
1	collector		
2	emitter	3 4	1
3	base		3 —
4	emitter	2 1	2, 4
			sym086

3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
BFG325/XR	SC-61AA	plastic surface mounted package; reverse pinning; 4 leads	SOT143R	

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
BFG325/XR	S2*

^{[1] * =} p: made in Hong Kong.

^[2] G_{max} is the maximum power gain, if K > 1. If K < 1 then G_{max} = MSG, see Figure 4.

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	15	V
V_{CEO}	collector-emitter voltage	open base		-	6	V
V _{EBO}	emitter-base voltage	open collector		-	2	V
I _C	collector current (DC)			-	35	mA
P _{tot}	total power dissipation	T _{sp} ≤ 90 °C	[1]	-	210	mW
T _{stg}	storage temperature			-65	+175	°C
T _j	junction temperature			-	175	°C

^[1] T_{sp} is the temperature at the soldering point of the collector pin.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point	$T_{sp} \le 90 ^{\circ}C$	<u>11</u> 405	K/W

^[1] T_{sp} is the temperature at the soldering point of the collector pin.

7. Characteristics

Table 7. Characteristics

 T_i = 25 °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$I_E = 0 A; V_{CB} = 5 V$	-	-	15	nA
h _{FE}	DC current gain	$I_C = 15 \text{ mA}; V_{CE} = 3 \text{ V}$	60	100	200	
C _{CBS}	collector-base capacitance	$V_{CB} = 5 \text{ V}$; f = 1 MHz; emitter grounded	-	0.26	0.4	рF
C _{CES}	collector-emitter capacitance	$V_{CE} = 5 \text{ V}$; f = 1 MHz; base grounded	-	0.27	-	рF
C _{EBS}	emitter-base capacitance	V _{EB} = 0.5 V; f = 1 MHz; collector grounded	-	0.53	-	рF
f _T	transition frequency	$I_C = 15 \text{ mA}; V_{CE} = 3 \text{ V}; f = 1 \text{ GHz};$ $T_{amb} = 25 \text{ °C}$	-	14	-	GHz
G _{max}	maximum power gain ^[1]	$I_C = 15 \text{ mA}; V_{CE} = 3 \text{ V}; f = 1.8 \text{ GHz};$ $T_{amb} = 25 \text{ °C}$	-	18.3	-	dB
$ s_{21} ^2$	insertion power gain	I_C = 15 mA; V_{CE} = 3 V; T_{amb} = 25 °C; Z_S = Z_L = 50 Ω				
		f = 1.8 GHz	-	14	-	dB
		f = 3 GHz	-	10	-	dB
NF	noise figure	Γ_{s} = Γ_{opt} ; I_{C} = 3 mA; V_{CE} = 3 V; f = 2 GHz	-	1.1	-	dB
$P_{L(1dB)} \\$	output power at 1 dB gain compression	I_C = 15 mA; V_{CE} = 3 V; f = 1.8 GHz; T_{amb} = 25 °C; Z_S = Z_L = 50 Ω	-	8.7	-	dBm
IP3	third order intercept point	$I_C = 15 \text{ mA}; V_{CE} = 3 \text{ V}; f = 1.8 \text{ GHz};$ $T_{amb} = 25 \text{ °C}; Z_S = Z_L = 50 \Omega$	-	19.4	-	dBm

BFG325_XF

[1] G_{max} is the maximum power gain, if K > 1. If K < 1 then $G_{max} = MSG$, see Figure 4.

$$\text{K is the Rollet stability factor: } K = \frac{I + \left| Ds \right|^2 - \left| s_{1I} \right|^2 - \left| s_{22} \right|^2}{2 \times \left| s_{2I} \right| \times \left| s_{12} \right|} \text{ where } Ds = s_{1I} \times s_{22} - s_{12} \times s_{2I} \, .$$

MSG = maximum stable gain.

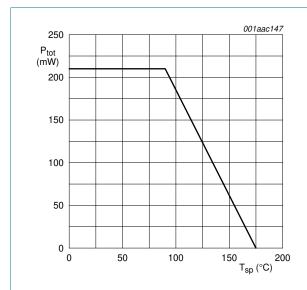


Fig 1. Power derating curve

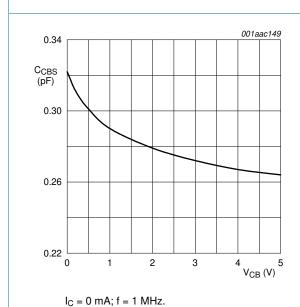


Fig 3. Collector-base capacitance as a function of collector-base voltage; typical values

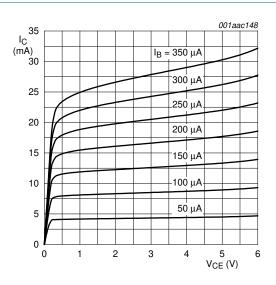
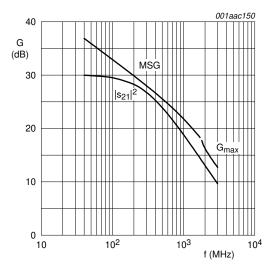


Fig 2. Collector current as a function of collector-emitter voltage; typical values



 $I_C = 15 \text{ mA}$; $V_{CE} = 3 \text{ V}$.

Fig 4. Gain as a function of frequency; typical values

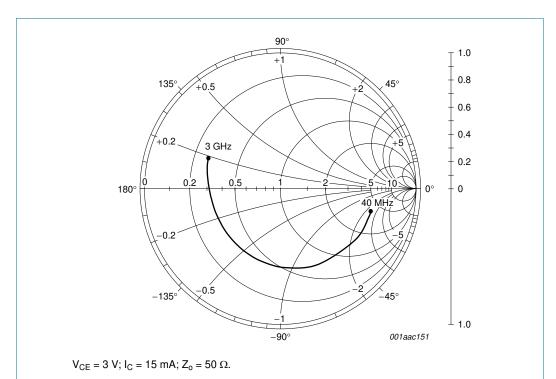


Fig 5. Common emitter input reflection coefficient (s₁₁); typical values

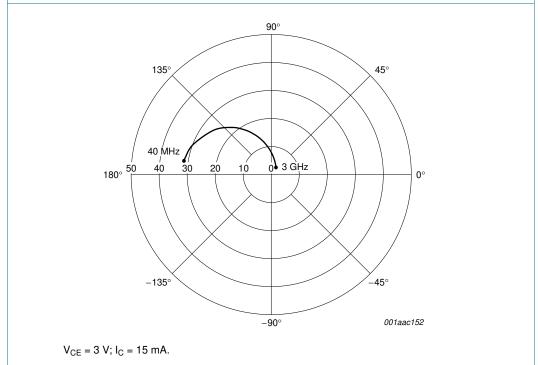


Fig 6. Common emitter forward transmission coefficient (s_{21}); typical values

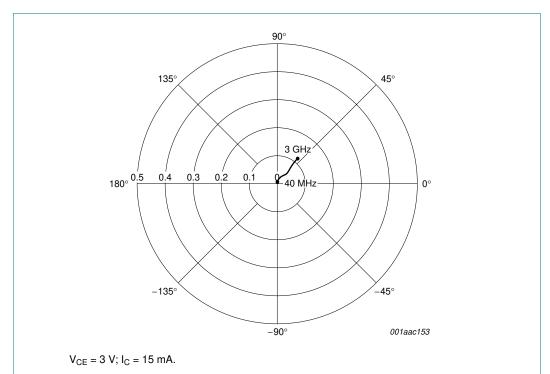


Fig 7. Common emitter reverse transmission coefficient (s_{12}) ; typical values

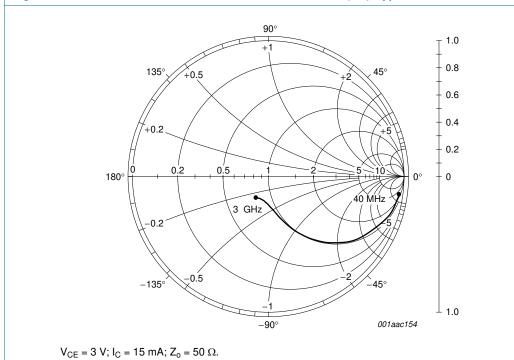


Fig 8. Common emitter output reflection coefficient (s₂₂); typical values

8. Application information

Table 8. SPICE parameters of the BFG325 DIE

Sequence	Parameter	Value	Unit
1	IS	26.6	аА
2	BF	200	-
3	NF	1	-
4	VAF	40	V
5	IKF	105	mA
6	ISE	2.3	fA
7	NE	2.114	-
8	BR	10	-
9	NR	1	-
10	VAR	2.5	V
11	IKR	10	Α
12	ISC	0	aA
13	NC	1.5	-
14	RB	3.6	Ω
15	RE	1.5	Ω
16	RC	2.6	Ω
17	CJE	185.6	fF
18	VJE	890	mV
19	MJE	0.294	-
20	CJC	77.06	fF
21	VJC	601	mV
22	MJC	0.159	-
23	XCJC	1	-
24	FC	0.7	-
25	TF	8.1	ps
26	XTF	10	-
27	VTF	1000	V
28	ITF	150	mA
29	PTF	0	deg
30	TR	0	ns
31	KF	0	-
32	AF	1	-
33	TNOM	25	°C
34	EG	1.014	eV
35	XTB	0	-
36	XTI	8	-
37	Q1.AREA	2.5	-

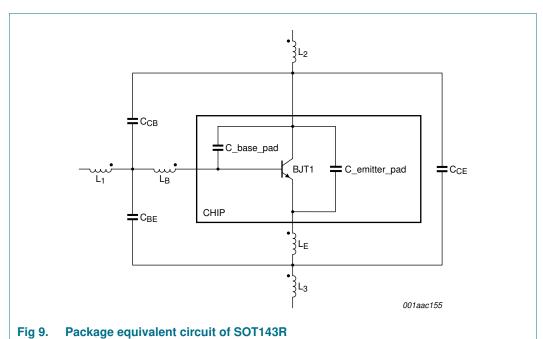


Table 9. List of components; see Figure 9

Designation	Value	Unit
C_{CB}	17	fF
C _{BE}	84	fF
C _{CE}	191	fF
C_base_pad	67	fF
C_emitter_pad	142	fF
L _B	0.95	nH
L _E	0.40	nH
L ₁	0.12	nH
L ₂	0.21	nH
L ₃	0.06	nH

9. Package outline

Plastic surface-mounted package; reverse pinning; 4 leads

SOT143R

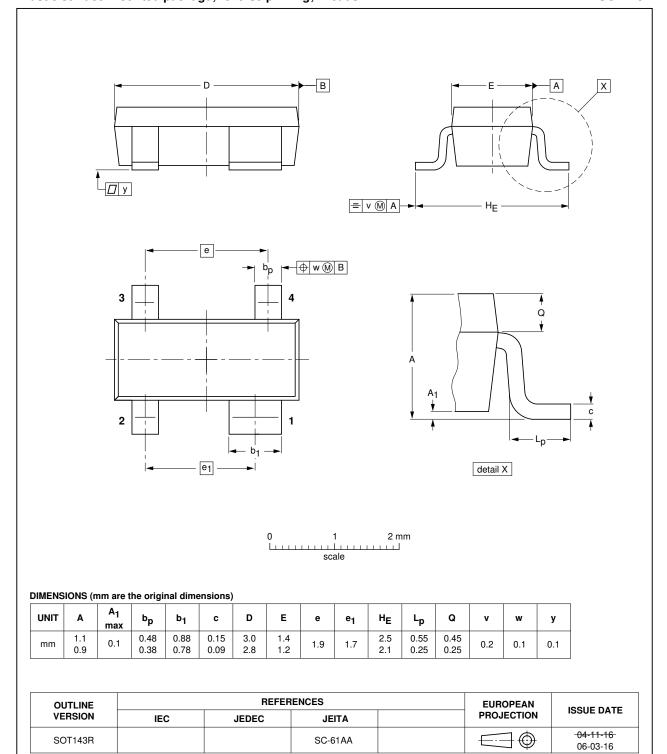


Fig 10. Package outline SOT143R (SC-61AA)



10. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BFG325_XR v.2	20110915	Product data sheet	-	BFG325_XR v.1
Modifications: • The format of guidelines of N • Legal texts have		of this data sheet has beer of NXP Semiconductors. have been adapted to the i utline drawings have been u	new company name whe	ere appropriate.
BFG325_XR v.1 (9397 750 14247)	20050202	Product data sheet	-	-

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11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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NXP Semiconductors BFG325/XR

NPN 14 GHz wideband transistor

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13. Contents

1	Product profile
1.1	General description
1.2	Features and benefits 1
1.3	Applications
1.4	Quick reference data 1
2	Pinning information 2
3	Ordering information 2
4	Marking 2
5	Limiting values 3
6	Thermal characteristics 3
7	Characteristics 3
8	Application information 7
9	Package outline
10	Revision history 10
11	Legal information
11.1	Data sheet status
11.2	Definitions
11.3	Disclaimers
11.4	Trademarks
12	Contact information 12
13	Contents 13

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